

Innovating Energy Technology

http://www.fujielectric.com/products/semiconductor/ Discrete IGBT

Discrete IGBT (High-Speed XS-series) 650V / 40A

Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA etc.)

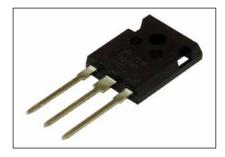
Applications

Uninterruptible power supply PV Power coditionner Inverter welding machine

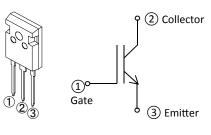
Maximum Ratings and Characteristics

● Absolute Maximum Ratings at T_{vi} = 25 °C (unless otherwise specified)

Parameter	Symbol	Value	Unit	Remarks
Collector-Emitter Voltage	VCES	650	V	
Gate-Emitter Voltage	V _{GES}	± 20	V	
Transient Gate-Emitter Voltage	VGES	± 30	v	t₀ < 1 µs
DC Collector Current	Ic@25	61	Α	<i>T</i> _c = 25 °C
	Ic@100	40	Α	<i>T</i> _c = 100 °C
Pulsed Collector Current	ICP	160	Α	Note *1
Turn-Off Safe Operating Area	-	160	А	V _{CE} ≤ 650 V T _{vj} ≤ 175 °C
Max. Power Dissipation	Ptot	234	W	<i>T</i> _c = 25 °C
Operating Junction Temperature	Tvj	-40 ~ +175	°C	
Storage Temperature	Tstg	-55 ~ +175	°C	



Equivalent circuit



TO-247-P2

Note *1 : Pulse width limited by T_{vj max}.

● Electrical Characteristics at T_{vi} = 25 °C (unless otherwise specified)

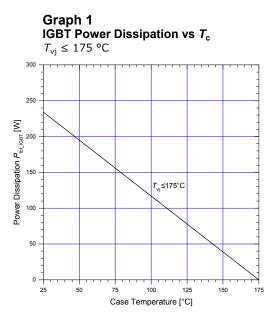
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Zero Gate Voltage	,	$V_{\rm CE} = 650 \text{ V}$ $T_{\rm vj} = 25 \text{ °C}$	-	-	250	μA
Collector Current	ICES	$V_{GE} = 0 V$ $T_{vj} = 175 ^{\circ}C$	-	-	2	mA
Gate-Emitter	Iges	$V_{CE} = 0 V$			200	nA
Leakage Current	IGES	$V_{\text{GE}} = \pm 20 \text{ V}$	-	-	200	ΠA
Gate-Emitter	V _{GE(th)}	V _{CE} = 20 V	3.4	4.0	4.6	V
Threshold Voltage	V GE(th)	/c = 40 mA	-	4.0	4.0	•
Collector-Emitter		$V_{GE} = 15 \text{ V}$ $T_{vj} = 25 \text{ °C}$	1.00	1.35	1.70	
Saturation Voltage	V _{CE(sat)}	$V_{c} = 40 \text{ A}$ $T_{vj} = 125 \text{ °C}$	-	1.50	-	V
oaturation voltage		$T_{\rm vj} = 175 ^{\circ}{\rm C}$	-	1.60	-	
Input Capacitance	Cies	V _{CE} = 25 V	1700	3400	5100	
Output Capacitance	Coes	$V_{\text{GE}} = 0 \text{ V}$	39	78	117	pF
Reverse Transfer Capacitance	Cres	f = 1 MHz	17	34	51	
		V _{cc} = 520 V				
Gate Charge	Q _G	$I_{\rm c} = 40 {\rm A}$	80	160	240	nC
		V _{GE} = 15 V				
Turn-On Delay Time	t _{d(on)}		14	28	42	
Rise Time	tr	$V_{\rm cc} = 400 \text{ V}$	8	16	24	ns
Turn-Off Delay Time	t _{d(off)}	/c = 20 A	100	200	300	115
Fall Time	tr	V _{GE} = 15 V 7.5		15	22.5	i
Turn-On Energy	Eon	R_{G} = 10 Ω 0.20 Energy loss include "tail" and FWD reverse recovery. 0.11		0.40	0.60	mJ
Turn-Off Energy	Eoff			0.30	0.45	ПJ
Turn-On Delay Time	t _{d(on)}	T _{vi} = 150 °C	14	28	42	
Rise Time	tr	$V_{cc} = 400 V$	11	22	33	-
Turn-Off Delay Time	t _{d(off)}	$I_{\rm c} = 20 {\rm A}$	120	240	360	ns
Fall Time	tr	V _{GE} = 15 V	11	22	33	
Turn-On Energy	Eon	$R_{\rm G} = 10 \ \Omega$	0.29	0.58	0.87	
Turn-Off Energy	Eoff	Energy loss include "tail" and FWD reverse recovery.	0.24	0.48	0.72	mJ

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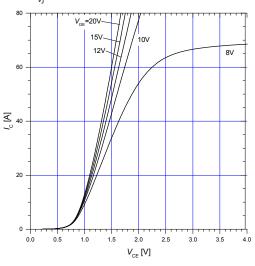
Thermal Resistance

Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction-Ambient	R _{th(j-a)}	-	-	50	°C/W
Thermal Resistance, Junction to Case	Rth(j-c)	-	-	0.642	°C/W

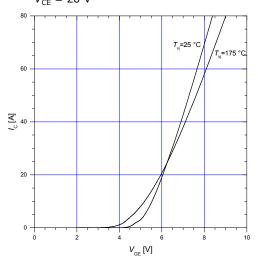
Characteristics (Representative)

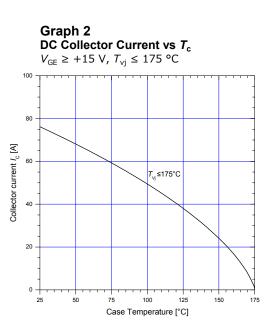




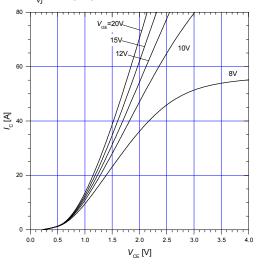


Graph 5 Typical transfer characteristics $V_{CE} = 20 \text{ V}$

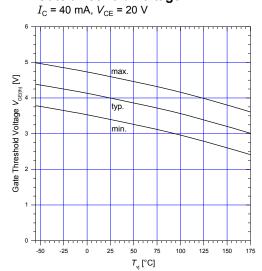


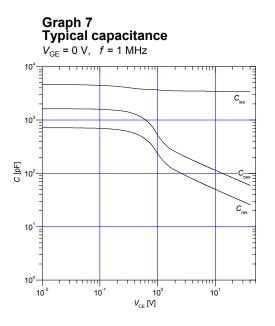


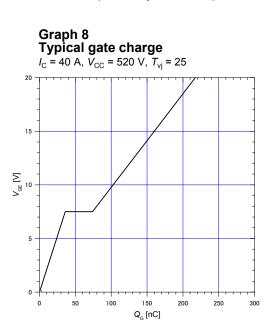


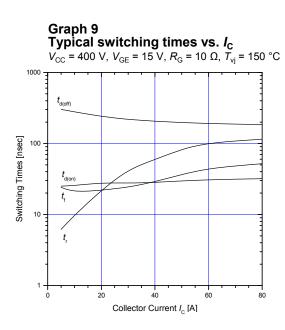


Graph 6 Gate threshold voltage

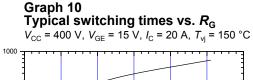


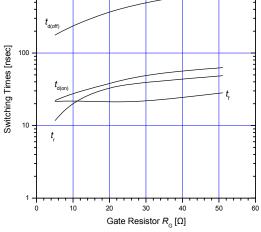


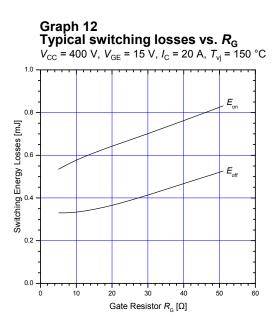




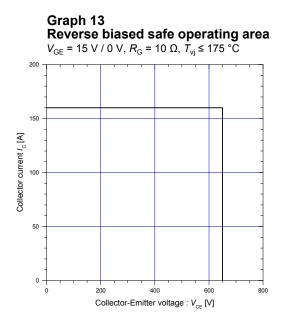
Graph 11 Typical switching losses vs. I_C $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, R_G = 10 \Omega, T_{vj} = 150 ^{\circ}\text{C}$

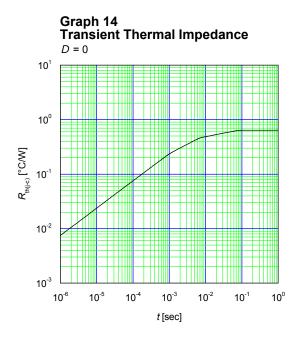




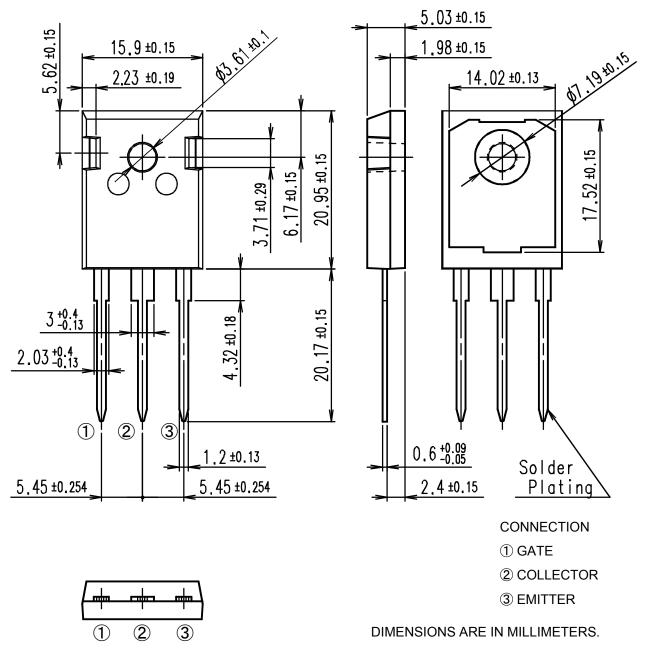


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Outline Drawings, mm



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